

PD1300-35D00-I
InGaAs PIN-Photodiode

PD1300-35D00-I is InGaAs PIN-Photodiode featuring excellent responsibility and high photocurrent for near infrared.

This PIN-Photodiode consists of a large chip with 0.35x0.35mm active area mounted on the TO-18 stem and is sealed by epoxy resin lens.

These devices are designed to be easy of setting up optically with a wide angle of half sensitivity of $\pm 60^\circ$.

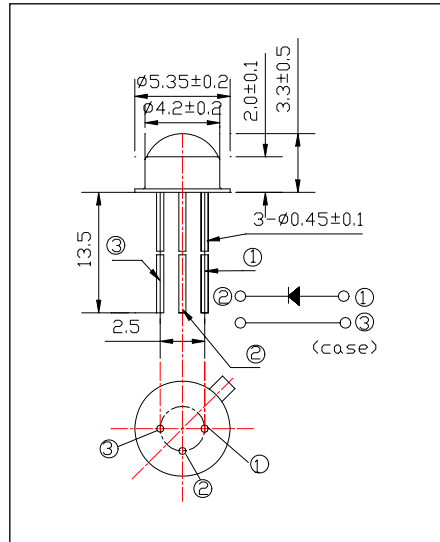
<Features>

- High Reliability
- High Response

<Specifications>

1. Product Name: InGaAs PIN-Photodio
2. Type Number: PD1300-35D00-I
3. Chip:
 - Active Area: 0.35mm x0.35mm
4. Package
 - Type: TO-18 (3pins)
 - Lens: Epoxy Resin Lens
 - Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	VR	10	V
Operating Temperature	TOPR	-20 ~ +90	°C
Storage Temperature	TSTG	-30 ~+100	°C
Soldering Temperature*	TSOL	260	°C

* Soldering condition must be completed within 2 seconds at 240°C

Electro-Optical Characteristics [Ta=25°C typ.]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Photo Responsibility	RE	VR=0V, λP =1300nm		0.9		A/W
Photo Current*	IL	VR=0V, λP =1300nm	10			μA
Dark Current	ID	VR=1V			100	nA
Spectral Responsibility(Peak)	λP	VR=0V	1000		1600	nm
Half Angle of Sensitivity	θ1/2	VR=0V		±60		deg
Total Capacitance	CT	F=1MHz, VR=1V		20		pF
Rise/Fall Time(10%~90%)	tr	RL=1kΩ, VR=1V		10		ns
	tf			5		

* Measured by Epitex's calibrated tool

